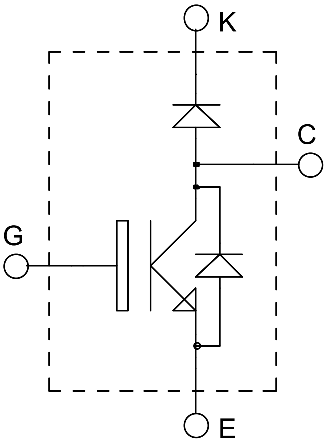
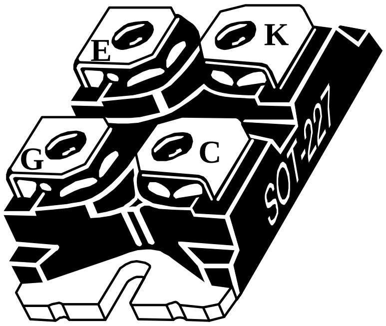
APT25GF120JCU2

ISOTOP® Boost chopper
NPT IGBT
SiC chopper diode

V_{CES} = 1200V
I_C = 25A @ Tc = 90°C





ISOTOP®

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- ***Non Punch Through (NPT) Fast IGBT***
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Low leakage current
  - RBSOA and SCSOA rated

- ***Chopper SiC Schottky Diode***
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF

- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	45	A
		T_C = 90°C	25	
I_{CM}	Pulsed Collector Current	T_C = 25°C	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	227	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	50A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
See application note APT0502 on www.microsemi.com

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All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 1200V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} =15V I_C = 25A	T_j = 25°C	2.5	3.2	3.7	V
			T_j = 125°C		4.0		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 1mA		4		6	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			1650		pF
C_{oes}	Output Capacitance				250		
C_{res}	Reverse Transfer Capacitance				110		
Q_g	Total gate Charge	V_{GE} = 15V V_{Bus} = 600V I_C =25A			160		nC
Q_{ge}	Gate – Emitter Charge				10		
Q_{gc}	Gate – Collector Charge				70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V V_{Bus} = 600V I_C = 25A R_G = 22Ω			60		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				305		
T_f	Fall Time				30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = 15V V_{Bus} = 600V I_C = 25A R_G = 22Ω			60		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				346		
T_f	Fall Time				40		
E_{on}	Turn-on Switching Energy	V_{GE} = 15V V_{Bus} = 600V I_C = 25A R_G = 22Ω	T_j = 125°C		2.1		mJ
E_{off}	Turn-off Switching Energy		T_j = 125°C		1.5		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 900V t_p≤ 10µs ; T_j = 125°C			150		A

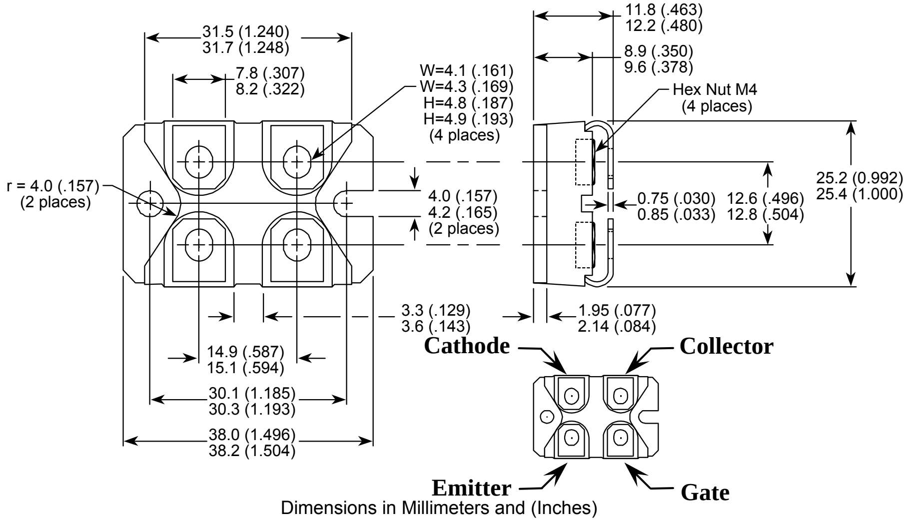
Chopper SiC diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C		32	200	µA
			T_j = 175°C		56	1000	
I_F	DC Forward Current		Tc = 125°C		10		A
V_F	Diode Forward Voltage	I_F = 10A	T_j = 25°C		1.6	1.8	V
			T_j = 175°C		2.3	3	
Q_C	Total Capacitive Charge	I_F = 10A, V_R = 600V di/dt =500A/µs			40		nC
C	Total Capacitance	f = 1MHz, V_R = 200V			96		pF
		f = 1MHz, V_R = 400V			69		

Thermal and package characteristics

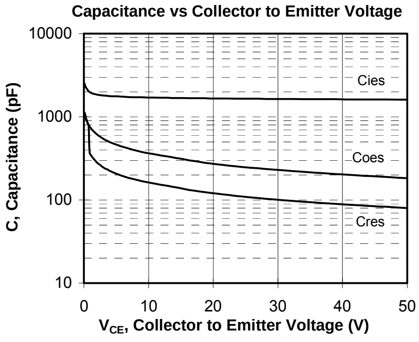
Symbol	*Characteristic*		*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance	IGBT			0.55	°C/W
		SiC chopper Diode			1.65	
R_{thJA}	Junction to Ambient (IGBT & Diode)				20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz		2500			V
T_J,T_{STG}	Storage Temperature Range		-55		150	°C
T_L	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

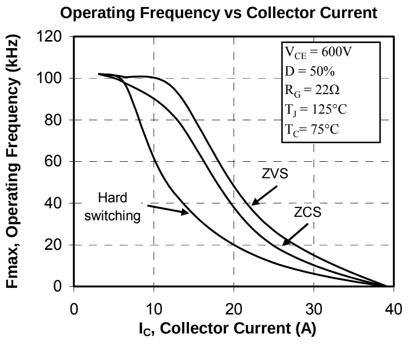
SOT-227 (ISOTOP®) Package Outline

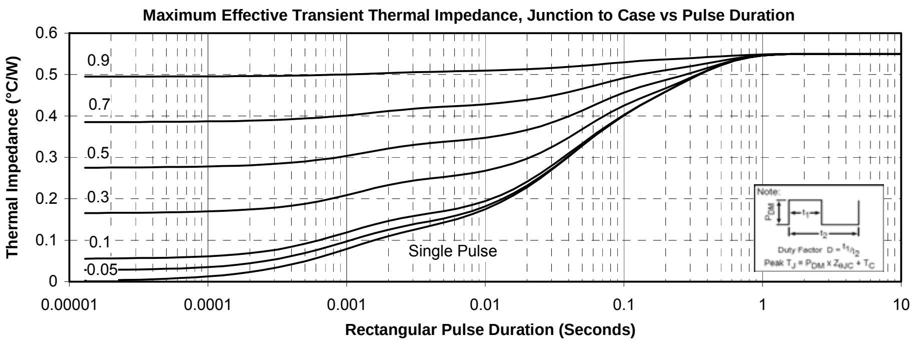


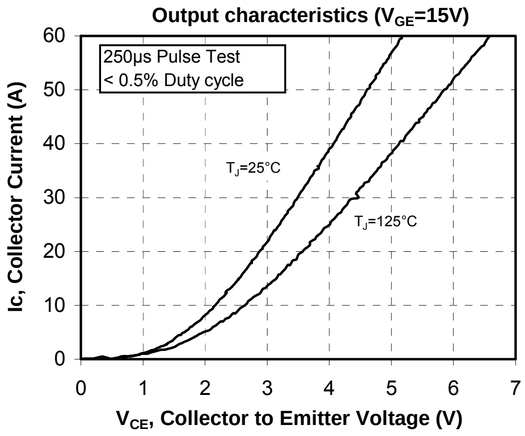
Dimensions in Millimeters and (Inches)

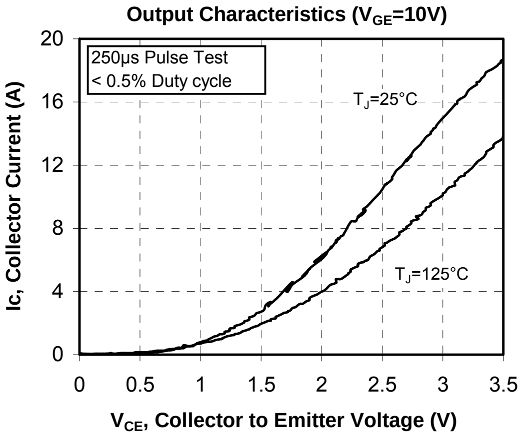
Typical IGBT Performance Curve

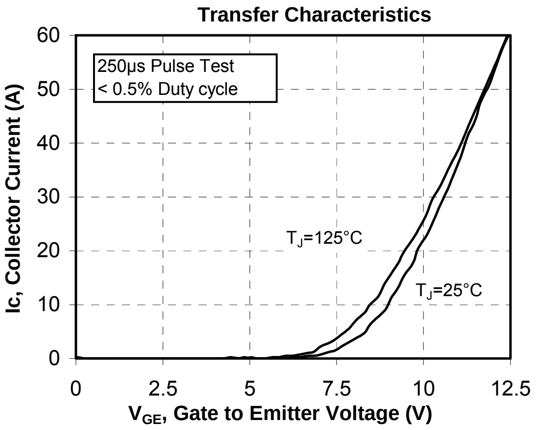

Capacitance vs Collector to Emitter Voltage

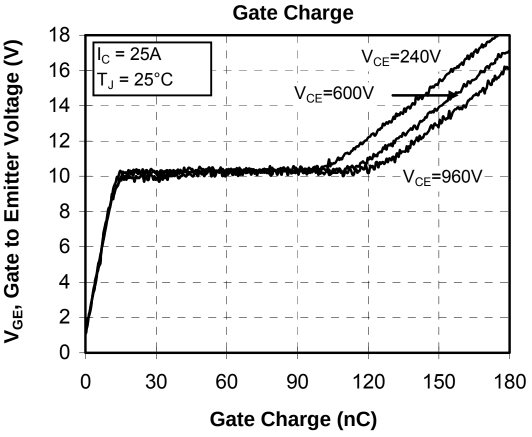

Operating Frequency vs Collector Current

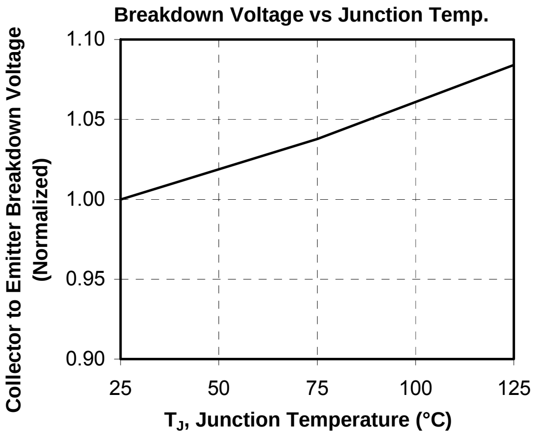

Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

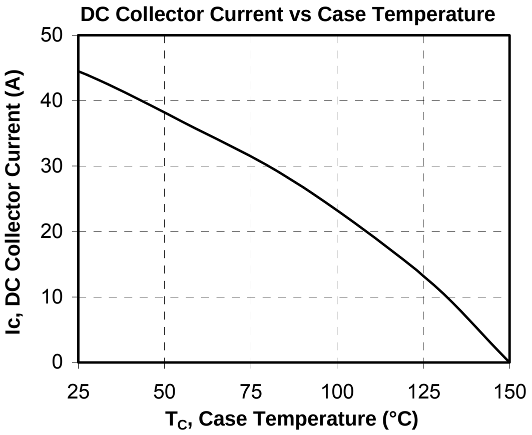

Output characteristics (V_{GE}=15V)


Output Characteristics (V_{GE}=10V)

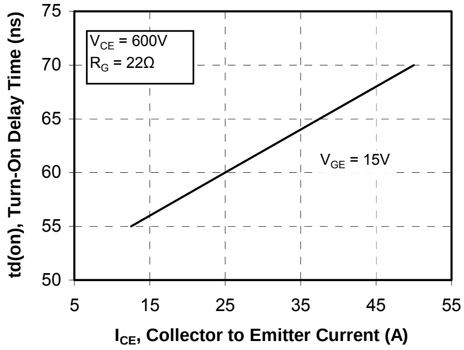

Transfer Characteristics


Gate Charge

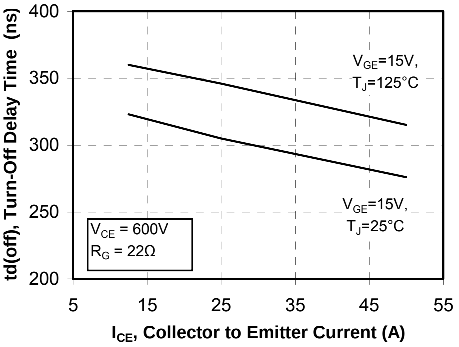

Breakdown Voltage vs Junction Temp.


DC Collector Current vs Case Temperature

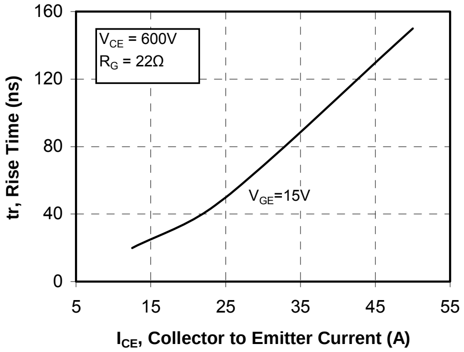
Turn-On Delay Time vs Collector Current



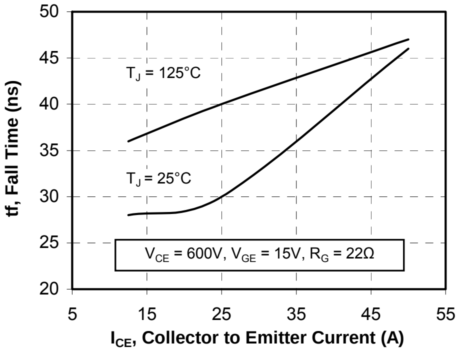
Turn-Off Delay Time vs Collector Current



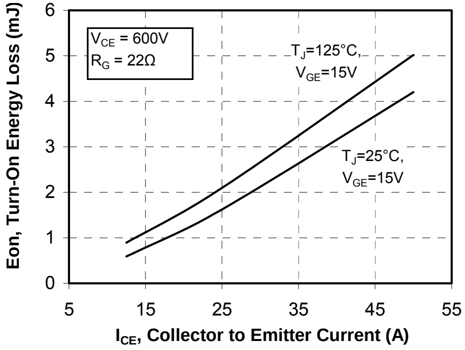
Current Rise Time vs Collector Current



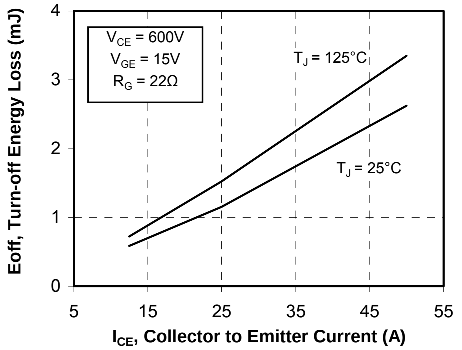
Current Fall Time vs Collector Current



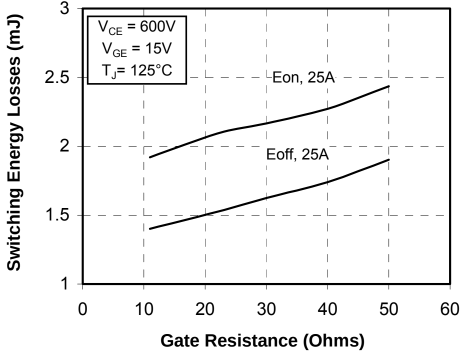
Turn-On Energy Loss vs Collector Current



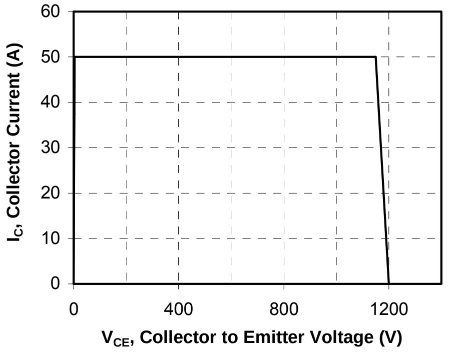
Turn-Off Energy Loss vs Collector Current



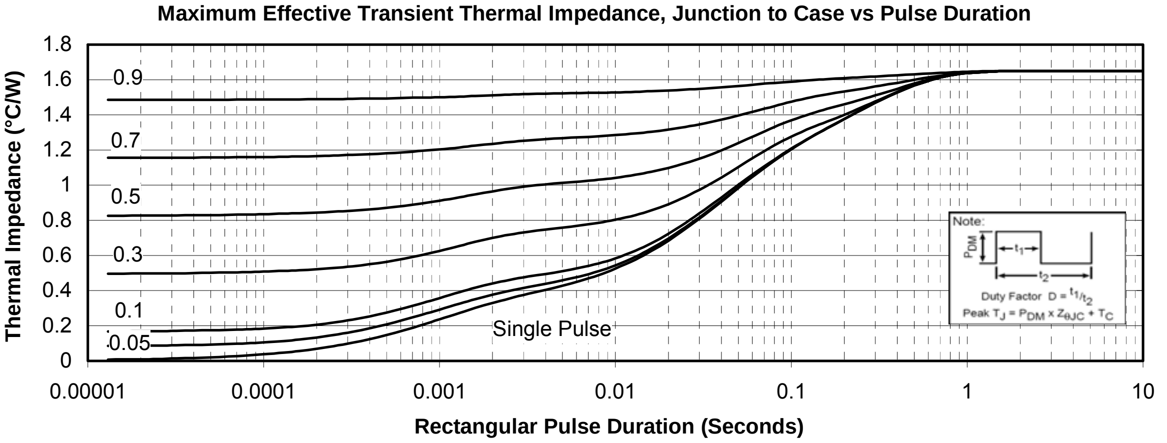
Switching Energy Losses vs Gate Resistance



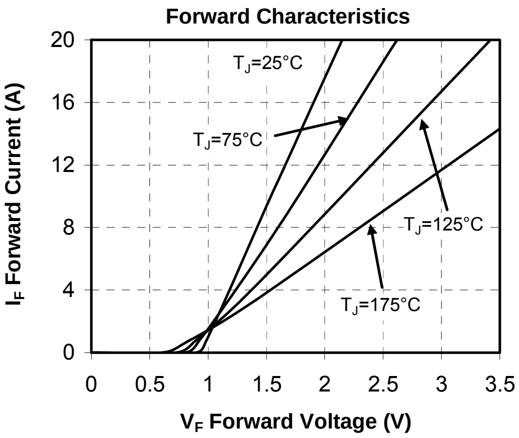
Reverse Bias Safe Operating Area



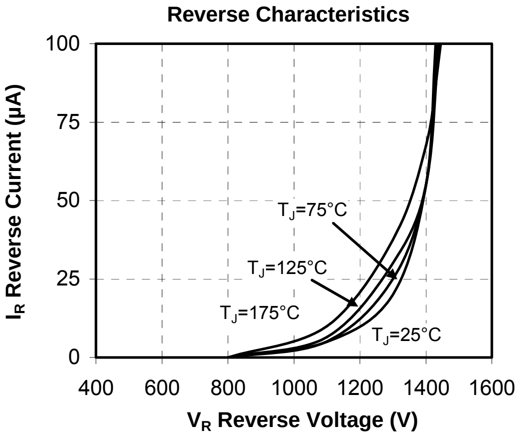
Typical SiC chopper diode Performance Curve



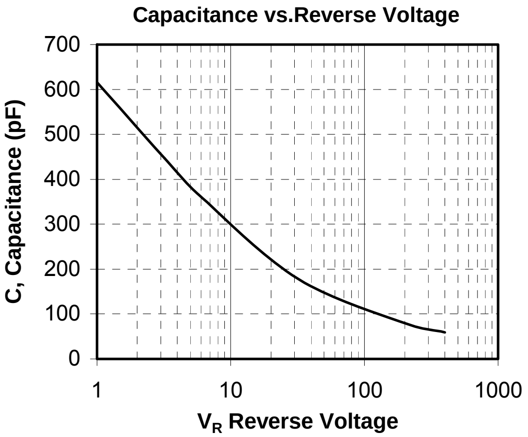
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Forward Characteristics



Reverse Characteristics



Capacitance vs.Reverse Voltage

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